

# PMEG3002AEL

30 V, 0.2 A very low  $V_F$  MEGA Schottky barrier rectifier in leadless ultra small SOD882 package

Rev. 01 — 24 February 2004

**Product data sheet** 



## 1. Product profile

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection encapsulated in a SOD882 leadless ultra small plastic package.

#### 1.2 Features

Forward current: 0.2 A

Reverse voltage: 30 V

- Very low forward voltage
- Leadless ultra small plastic package
- Power dissipation comparable to SOT23.

#### 1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Low power consumption applications.

#### 1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current		-	-	0.2	Α
$V_R$	reverse voltage		-	-	30	V



## 2. Pinning information

Table 2: Discrete pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	. 84
2	anode	1 D 2 Bottom view Top view 001aaa332	1 <del>[4]</del> 2 sym001

<sup>[1]</sup> The marking bar indicates the cathode.

## 3. Ordering information

**Table 3: Ordering information** 

Type number	Package		
	Name	Description	Version
PMEG3002AEL	-	leadless ultra small plastic package; 2 terminals; body $1.0 \times 0.6 \times 0.5$ mm	SOD882

# 4. Marking

Table 4: Marking

Type number	Marking code
PMEG3002AEL	F3

# 5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{R}$	continuous reverse voltage			-	30	V
I <sub>F</sub>	continuous forward current			-	0.2	Α
$I_{FRM}$	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$		-	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8 ms square wave		-	3	Α
Tj	junction temperature		[1]	-	150	°C
$T_{amb}$	operating ambient temperature		[1]	-65	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

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[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses. Nomograms for determining the reverse power losses  $P_R$  and  $I_{F(AV)}$  rating will be available on request.

### 6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1][2] 500	K/W

- [1] Refer to SOD882 standard mounting conditions (footprint), FR4 with 60 µm copper strip line.
- [2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determining the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating will be available on request.

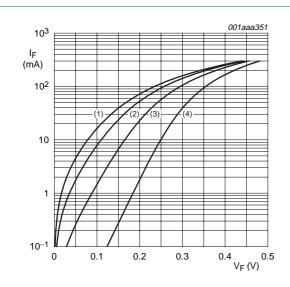
#### 7. Characteristics

Table 7: Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified

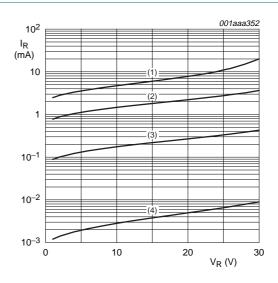
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>F</sub>	continuous forward voltage	see Figure 1;					
		$I_F = 0.1 \text{ mA}$		-	125	190	mV
		I <sub>F</sub> = 1 mA		-	185	250	mV
		I <sub>F</sub> = 10 mA		-	250	300	mV
		I <sub>F</sub> = 100 mA		-	350	400	mV
		$I_F = 200 \text{ mA}$		-	420	480	mV
I <sub>R</sub>	continuous reverse current	see Figure 2;	<u>[1]</u>				
		V <sub>R</sub> = 10 V		-	2.5	10	μΑ
		V <sub>R</sub> = 30 V		-	10	50	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 1 \text{ V; } f = 1 \text{ MHz;}$ see Figure 3		-	17	25	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



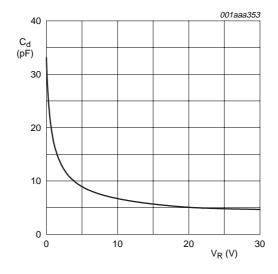
- (1)  $T_i = 150 \,^{\circ}\text{C}$ .
- (2)  $T_i = 125 \,^{\circ}\text{C}$ .
- (3)  $T_i = 85 \,^{\circ}\text{C}$ .
- (4)  $T_j = 25 \, ^{\circ}C$ .

Fig 1. Forward current as a function of forward voltage; typical values.



- (1)  $T_i = 150 \,^{\circ}\text{C}$ .
- (2)  $T_i = 125 \,^{\circ}\text{C}$ .
- (3)  $T_i = 85 \,^{\circ}\text{C}$ .
- (4)  $T_j = 25 \,^{\circ}\text{C}$ .

Fig 2. Reverse current as a function of reverse voltage; typical values.



 $T_{amb} = 25 \, ^{\circ}C$ ;  $f = 1 \, MHz$ .

Fig 3. Diode capacitance as a function of reverse voltage; typical values.

## 8. Package outline

Leadless ultra small plastic package; 2 terminals; body 1.0 x 0.6 x 0.5 mm

SOD882

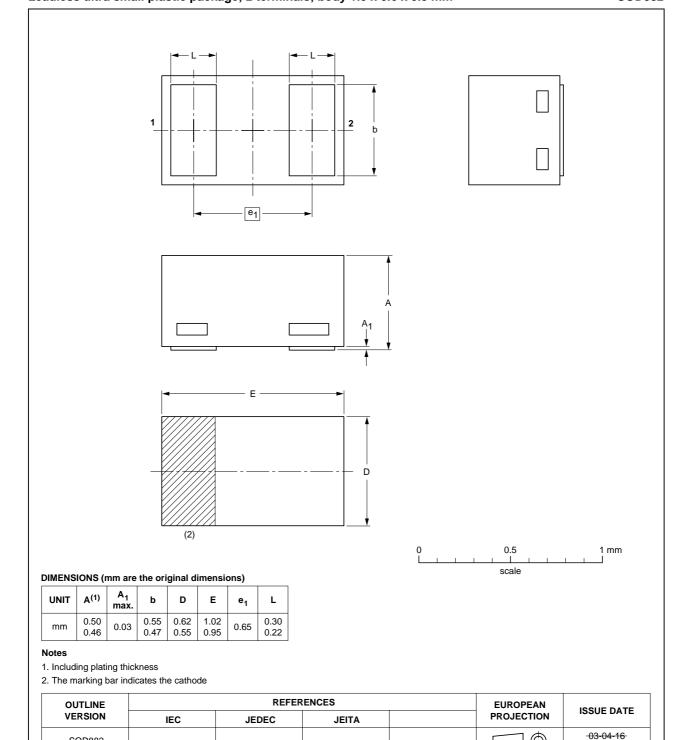


Fig 4. Package outline.

SOD882

03-04-17

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# 9. Revision history

## Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMEG3002AEL_1	20040224	Product data	-	9397 750 12466	-

**Product data sheet** 



Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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# PMEG3002AEL

0.2 A very low V<sub>F</sub> MEGA Schottky barrier rectifier

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